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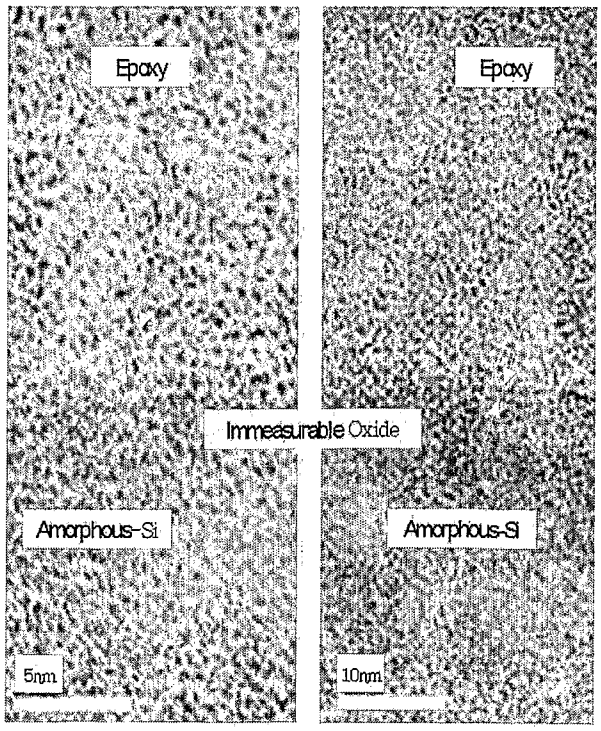
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(54) Title: METHOD FOR REMOVING PHOTORESIST IN SEMICONDUCTOR MANUFACTURING PROCESS



(57) Abstract: Disclosed herein is a method for removing a photoresist in a semiconductor manufacturing process wherein the removal of a photoresist, i.e. ashing, is carried out using plasma generated from a hydrogen (H_2)-containing mixed gas. According to the method, the formation of a silicon oxide film can be minimized, thereby preventing silicon loss without no popping, even residues of a high-dose ion implanted DUV photoresist can be completely removed, and further ashing efficiency can be enhanced.

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